

<b>Notice of References Cited</b>	Application/Control No. 10/711,004	Applicant(s)/Patent Under Reexamination CHANG, KENT KUOHUA	
	Examiner Maria Guerrero	Art Unit 2822	Page 1 of 1

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	B	US-6,468,865	10-2002	Yang et al.	438/262
	C	US-			
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	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kang et al. "Improved Thermal Stability and device performance of ultra-thin (EOT<10A) gate dielectric MOSFETs by using hafnium oxynitride (HfOxNy)"; June 2002; IEEE, pages 146-147.
	V	Laaksonen et al. "Advanced CMOS transistors with a novel HfSiON gate dielectric", June 2002, IEEE, pages 148-149.
	W	Rotondaro et al. "Carrier mobility in MOSFETs fabricated with Hf-Si-O-N gate dielectric, polysilicon gate electrode, and self-aligned source and drain"; October 2002, pages 603-605.
	X	Shanware et al. "Reliability evaluation of HfSiON gate dielectric film with 12.8 a SiO2 equivalent thickness"; December 2001

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.